

MJE13003VK5 (3DD13003VK5)

硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途：耐压高，开关速度快，安全工作区宽，符合 RoHS 规范。

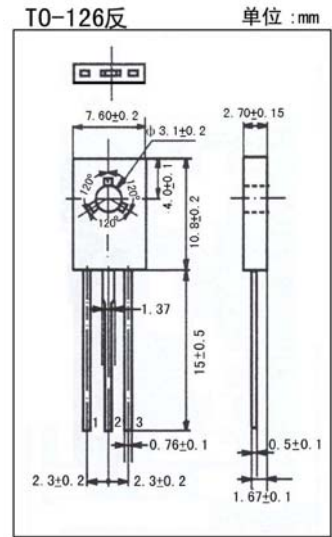
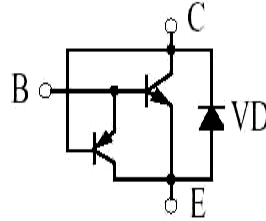
Purpose: High voltage capability, high speed switching, wide soa, RoHS compliant.

特点：适用于 110V 电路、节能灯、电子镇流器。

Features: Suitable for 110V circuit mode, fluorescent lamp, electronic ballast.

极限参数/Absolute maximum ratings(Tc=25°C)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CBO}	400	V
V _{CEO}	200	V
V _{EBO}	9.0	V
I _C	3.0	A
P _C	1.25	W
P _C (Tc=25°C)	20	W
T _j	150	°C
T _{stg}	-55~150	°C



引脚：1. B 2. C 3. E

电性能参数/Electrical characteristics(Tc=25°C)

参数符号 Symbol	测试条件 Test Condition		数值 Rating			单位 Unit
			最小值 Min	典型值 Typ	最大值 Max	
V _{CBO}	I _C =1mA	I _E =0	400			V
V _{CEO}	I _C =10mA	I _B =0	200			V
V _{EBO}	I _E =1mA	I _C =0	9.0			V
I _{CBO}	V _{CB} =400V	I _E =0			0.1	mA
I _{CEO}	V _{CE} =200V	I _B =0			0.1	mA
I _{EBO}	V _{EB} =9.0V	I _C =0			0.1	mA
h _{FE(1)}	V _{CE} =5.0V	I _C =0.2A	10		40	
h _{FE(2)}	V _{CE} =5.0V	I _C =0.001A	7.0			
h _{FE(3)}	V _{CE} =5.0V	I _C =3.0A	5.0			
V _{CE(sat) (1)}	I _C =2.5A	I _B =0.5A			1.5	V
V _{CE(sat) (2)}	I _C =1.0A	I _B =0.2A			0.5	V
V _{BE(sat)}	I _C =2.5A	I _B =0.5A			1.5	V
t _s	V _{CE} =5V I _C =0.25A (UI9600)		1.5		3.5	μs
t _F					0.6	μs
f _T	V _{CE} =10V I _C =0.2A f=1MHz		5			MHz

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